

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVF100** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	35 °C/W

PACKAGE STYLE .250 2L FLG (B)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

ORDER CODE: ASI10569

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _E = 28 V			5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			80	pF
P_G η_c	V _{CC} = 40 V P _{OUT} = 100 W f = 1030 - 1090 MHz	10 35			dB %